

DMN2005K

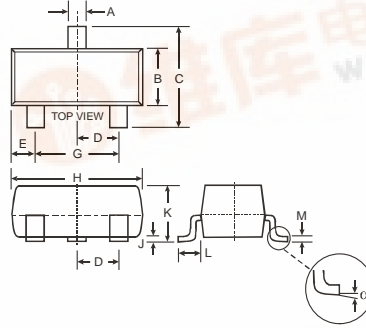
N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

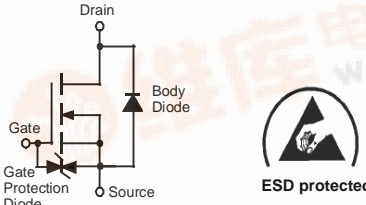
- Low On-Resistance
- Very Low Gate Threshold Voltage, 0.9V Max.
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **Lead Free By Design/RoHS Compliant (Note 2)**
- **"Green" Device (Note 4)**
- **ESD Protected Gate**

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking: See Page 4
- Ordering & Date Code Information: See Page 4
- Weight: 0.008 grams (approximate)



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
α	0°	8°



EQUIVALENT CIRCUIT

Maximum Ratings @_{T_A} = 25°C unless otherwise specified

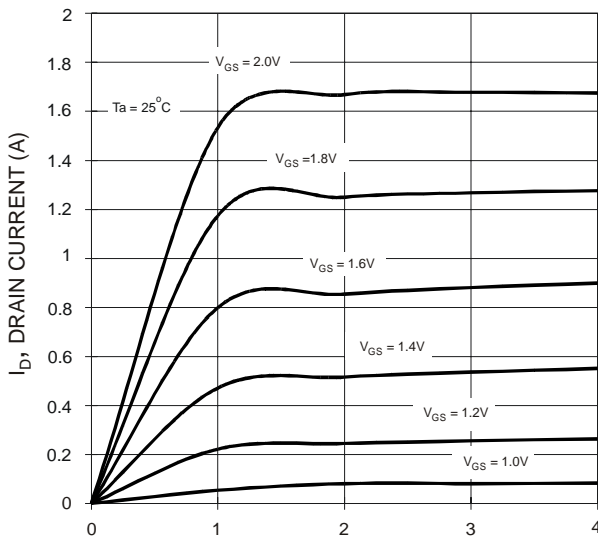
Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	20	V
Gate-Source Voltage	V _{GSS}	±10	V
Drain Current per element (Note 1)	I _D	300	mA
Continuous Pulsed (Note 3)		600	
Total Power Dissipation (Note 1)	P _d	350	mW
Thermal Resistance, Junction to Ambient	R _{θJA}	357	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-65 to +150	°C

- Notes:
1. Device mounted on FR-4 PCB.
 2. No purposefully added lead.
 3. Pulse width ≤10μs, Duty Cycle ≤1%.
 4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

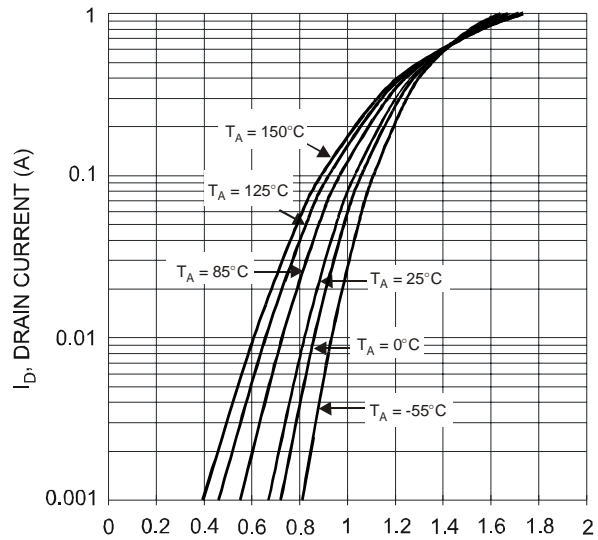
Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	—	—	V	$V_{GS} = 0V, I_D = 100\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	10	μA	$V_{DS} = 17V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	—	—	± 5	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	$V_{GS(th)}$	0.53	—	0.9	V	$V_{DS} = V_{GS}, I_D = 100\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	—	3.5 1.7	Ω	$V_{GS} = 1.8V, I_D = 200\text{mA}$ $V_{GS} = 2.7V, I_D = 200\text{mA}$
Forward Transfer Admittance	$ Y_{fs} $	40	—	—	mS	$V_{DS} = 3V, I_D = 10A$

Notes: 5. Short duration test pulse used to minimize self-heating effect.



V_{DS} , DRAIN-SOURCE VOLTAGE (V)
Fig. 1 Typical Output Characteristics



V_{GS} , GATE-SOURCE VOLTAGE (V)
Fig. 2 Reverse Drain Current vs. Source-Drain Voltage

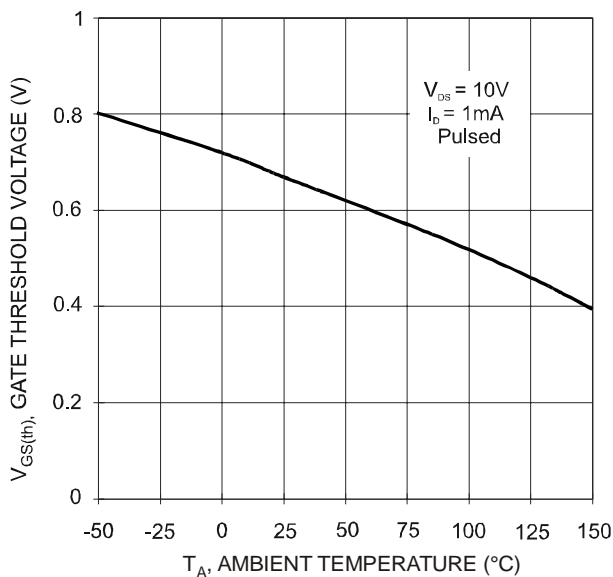


Fig. 3 Gate Threshold Voltage vs. Ambient Temperature

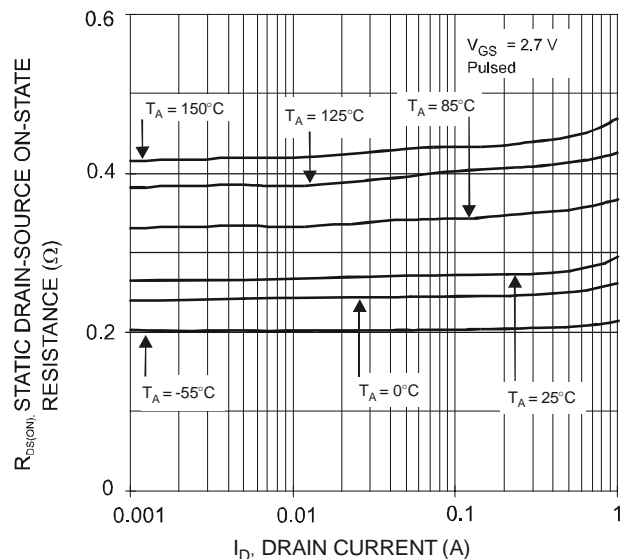


Fig. 4 Static Drain-Source On-State Resistance vs. Drain Current

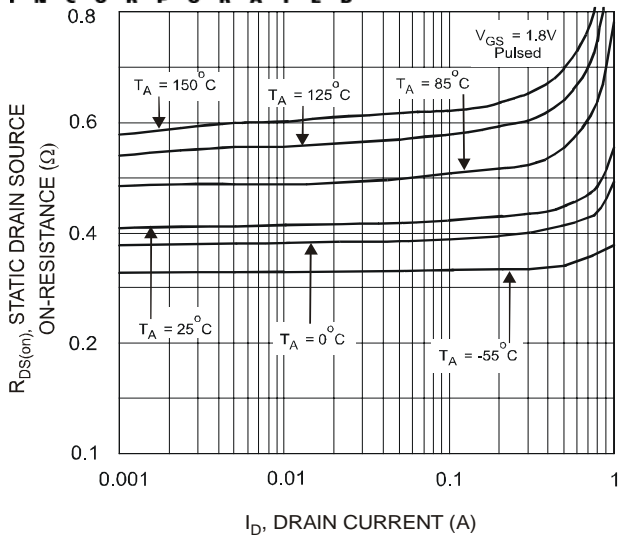


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

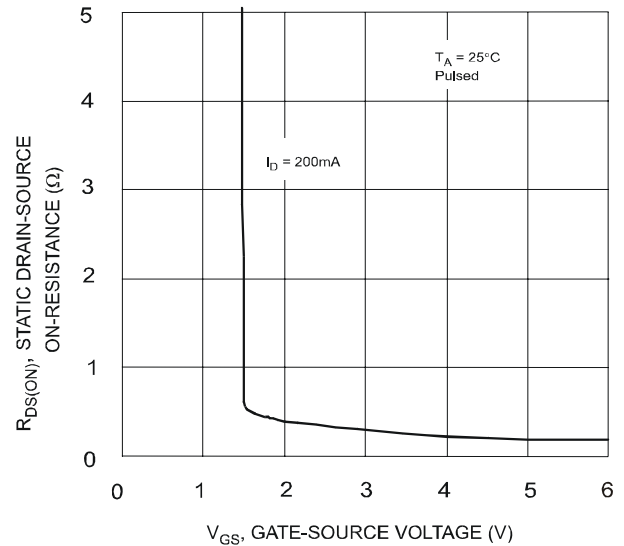


Fig. 6 Static Drain-Source, On-Resistance vs. Gate-Source Voltage

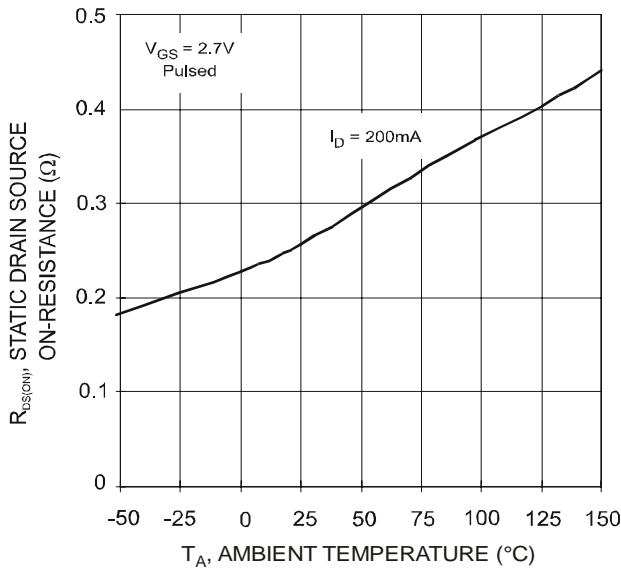


Fig. 7 Static Drain-Source, On-Resistance vs. Ambient Temperature

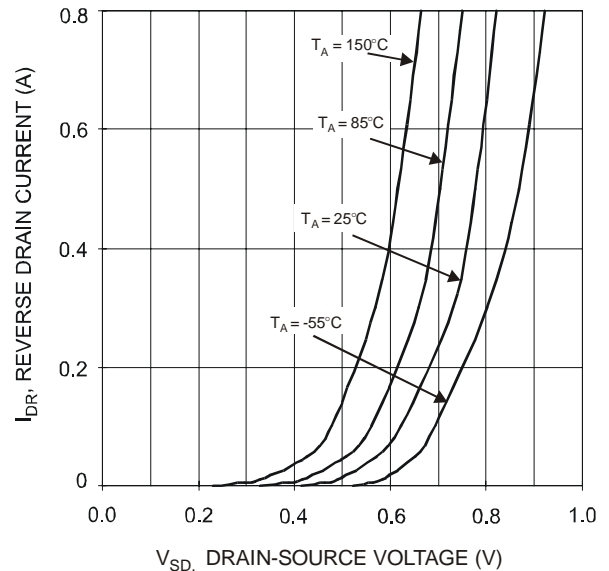


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

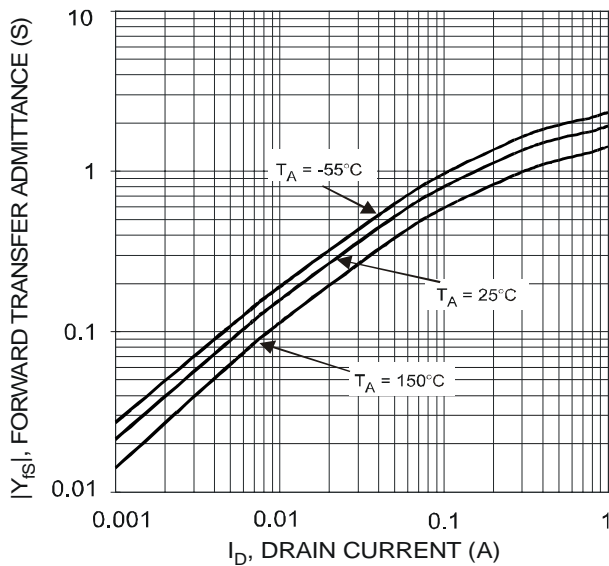


Fig. 9 Forward Transfer Admittance vs. Drain Current

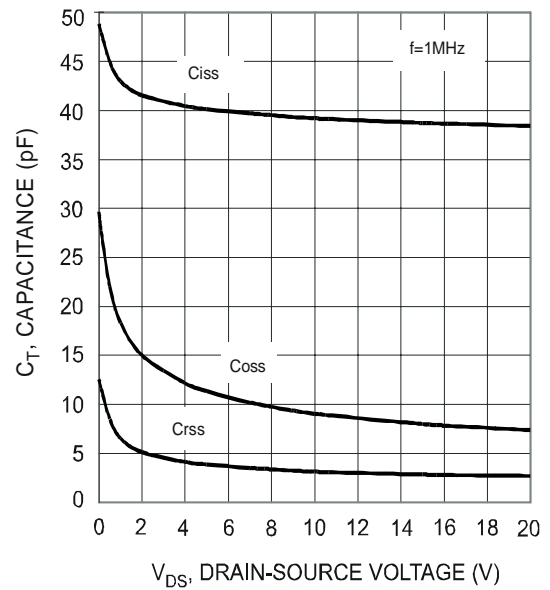


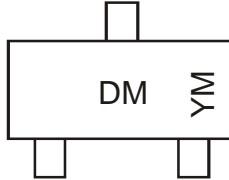
Fig. 10 Typical Capacitance

Ordering Information (Note 6)

Device	Packaging	Shipping
DMN2005K-7	SOT-23	3000/Tape & Reel

Notes: 6. For packaging details, please go to our website at <http://www.diodes.com/ap02007.pdf>.

Marking Information



DM = Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: T = 2006
 M = Month ex: 9 = September

Date Code Key

Year	2006	2007	2008	2009	2010	2011	2012
Code	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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